

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-8. (Cancelled)

9. (New) A method for producing at least one of (a) etched holes and (b) etched trenches of a component based on one of (c) silicon and (d) a layered silicon/insulator structure, the method comprising:

providing at least one of a germanium-containing layer and a germanium layer at a point at which or in whose surroundings an etching procedure is to be completed;

detecting at least one of germanium and germanium compounds during the etching procedure; and

controlling the etching procedure as a function of the detection.

10. (New) The method according to claim 9, wherein the controlling includes interrupting the etching procedure.

11. (New) The method according to claim 9, wherein at least one of the germanium and germanium-containing layer is buried in a layered structure.

12. (New) The method according to claim 9, further comprising applying at least one of the germanium and germanium-containing layer to a back of a silicon wafer.

13. (New) The method according to claim 9, further comprising removing at least one of the germanium and germanium-containing layer after completion of a etching procedure up to at least one of the germanium and germanium-containing layer.

14. (New) The method according to claim 9, wherein at least one of the germanium and germanium-containing layer is simultaneously used as a component functional layer.

15. (New) The method according to claim 9, wherein the at least one of germanium and germanium compounds is detected using one of optical emission spectroscopy and mass spectroscopy.

16. (New) A diaphragm sensor unit comprising:

a substrate made of one of silicon and a layered silicon/insulator structure; and

a flat diaphragm for implementing a sensor element structure for a sensor,

wherein at least one of a germanium and germanium-containing layer is situated in the layered structure.

17. (New) The diaphragm sensor unit according to claim 16, wherein the flat diaphragm contains germanium.

18. (New) The diaphragm sensor unit according to claim 16, wherein the flat diaphragm is made entirely of germanium.